Adel Ashery

List of Publications by Year
in descending order

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60	737	643344	721071
papers	citations	15 h-index	23 g-index

60	60	60	481
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Optical absorption and spectrophotometric studies on the optical constants and dielectric of poly (o-toluidine) (POT) films grown by spin coating deposition. Physica B: Condensed Matter, 2012, 407, 2404-2411.	1.3	67
2	Effect of temperature, illumination and frequency on the electrical characteristics of Cu/p-Si Schottky diode prepared by liquid phase epitaxy. Journal of Alloys and Compounds, 2010, 495, 116-120.	2.8	52
3	Optical dispersion and electronic transition characterizations of spin coated polyaniline thin films. Synthetic Metals, 2010, 160, 156-161.	2.1	42
4	Optical absorption and dispersion analysis based on single-oscillator model of polypyrrole (PPy) thin film. Synthetic Metals, 2012, 162, 1357-1363.	2.1	40
5	Structural, electrical and magnetic characterizations of Ni/Cu/p-Si Schottky diodes prepared by liquid phase epitaxy. Microelectronic Engineering, 2010, 87, 2218-2224.	1.1	30
6	Structural and electrical characteristics of n-InSb/p-GaAs heterojunction prepared by liquid phase epitaxy. Journal of Alloys and Compounds, 2014, 615, 604-609.	2.8	26
7	Enhancement of electrical and dielectrically performance of graphene-based promise electronic devices. Synthetic Metals, 2020, 261, 116303.	2.1	24
8	Investigation of electrical and capacitance- voltage characteristics of GO/TiO2/n-Si MOS device. Materials Science in Semiconductor Processing, 2020, 114, 105070.	1.9	22
9	Negative resistance, capacitance in Mn/SiO₂/p-Si MOS structure. Materials Research Express, 2020, 7, 085901.	0.8	20
10	Electrical and Dielectric Characterizations of Cu2ZnSnSe4/n-Si Heterojunction. Silicon, 2019, 11, 2567-2574.	1.8	19
11	Electrical performance of nanocrystalline graphene oxide/SiO2-based hybrid heterojunction device. Materials Science in Semiconductor Processing, 2021, 121, 105415.	1.9	19
12	Fabrication and characterization of in situ polymerized n-polyaniline films grown on p-Si heterojunctions. Microelectronic Engineering, 2008, 85, 2309-2315.	1.1	18
13	Investigation of electrical and dielectric properties of epitaxially grown Au/n-GaAs/p-Si/Al heterojunction. Optical and Quantum Electronics, 2020, 52, 1.	1.5	18
14	Frequency and temperature dependence of dielectric properties and capacitanceâ€“voltage in GO/TiO2/n-Si MOS device. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	1.1	17
15	Structural, electrical and phototransient characteristics of liquid phase epitaxial GaP based heterojunction for photodiode application. Superlattices and Microstructures, 2014, 66, 136-147.	1.4	16
16	Electrical, dielectric characterizations and optoelectronic applications of epitaxially grown Co/n-CuO/p-Si heterojunctions. Superlattices and Microstructures, 2019, 135, 106277.	1.4	16
17	Heterostructure Device Based on Graphene Oxide/TiO2/n-Si for Optoelectronic Applications. ECS Journal of Solid State Science and Technology, 2021, 10, 021002.	0.9	16
18	Analysis of Electrical and Capacitanceâ€“Voltage of PVA/nSi. Journal of Electronic Materials, 2021, 50, 3498-3516.	1.0	16

#	Article	IF	Citations
19	Fabrication and electrical characterization of the Al/n-Si/CZTSe4/Ag heterojunction. Physica B: Condensed Matter, 2021, 609, 412707.	1.3	15
20	Analysis of electrical, dielectric and thermal performance of NiFe/SiO2/Si MOS device fabricated by liquid phase epitaxy. Materials Science in Semiconductor Processing, 2019, 104, 104652.	1.9	14
21	Current Transport and Dielectric Analysis of Ni/SiO2/P-Si Diode Prepared by Liquid Phase Epitaxy. Silicon, 2022, 14, 153-163.	1.8	14
22	Enhancement of Electrical and Dielectric Properties of Graphene Oxideâ€nanoparticle Based Devices. Silicon, 2022, 14, 1913-1924.	1.8	13
23	Negative Capacitance, Negative Resistance in CNT/TiO2/SiO2/p-Si Heterostructure for Light-Emitting Diode Applications. ECS Journal of Solid State Science and Technology, 2021, 10, 031006.	0.9	13
24	Dielectric and electrical performance of poly (o-toluidine) based MOS devices. Physica B: Condensed Matter, 2021, 618, 413204.	1.3	13
25	Synthesis, characterization and electrical properties of conducting nanoparticles of graphene oxide. Materials Today: Proceedings, 2021, 44, 3017-3024.	0.9	13
26	Currentâ€“voltageâ€“temperature characteristics and magnetic response of Co/n-CuO/p-Si/Al heterojunction diode. Superlattices and Microstructures, 2014, 71, 275-284.	1.4	12
27	Tailoring the electrical characterization of epitaxialCuInGaSe2 thin film-based device for photodiode appliances. Superlattices and Microstructures, 2020, 142, 106505.	1.4	12
28	Novel negative capacitance, conductance at high and low frequencies in Au/Polypyrrole â€“MWCNT composite /TiO₂/Al₂O₃/n-Si structure. Materials Research Express, 2021, 8, 075003.	0.8	11
29	Structural and optical characteristics of PEDOT/n-Si heterojunction diode. Synthetic Metals, 2016, 214, 92-99.	2.1	10
30	Electrical performance and photosensitive properties of Cu/SiO2/Si â€“MOS based junction prepared by liquid phase epitaxy. Superlattices and Microstructures, 2017, 109, 662-674.	1.4	10
31	Fabrication and electrical characterization of n-InSb on porous Si heterojunctions prepared by liquid phase epitaxy. Microelectronics Journal, 2008, 39, 253-260.	1.1	9
32	Fabrication, Electrical and Dielectric Characterization of Au/CNT/TiO₂/SiO₂/p-Si/Al with High Dielectric Constant, Low Loss Dielectric Tangent. ECS Journal of Solid State Science and Technology, 2021, 10, 051003.	0.9	8
33	Nanostructural, optical and heterojunction characteristics of PEDOTâ„¢/ZnO nanocomposite thin films. Journal of Alloys and Compounds, 2017, 723, 276-287.	2.8	7
34	Dielectric Assessment of Epitaxially Grown Al/SiO2/Si Heterojunction. Silicon, 2019, 11, 1875-1883.	1.8	7
35	Frequency and Voltage Dependence of the Dielectric Properties of Ni/SiO2/P-Si (MOS) Structure. Silicon, 2020, 12, 1879-1885.	1.8	7
36	Current Transport, Photosensitive, and Dielectric Properties of PVA/n-Si Heterojunction Photodiode. Silicon, 0, , 1.	1.8	7

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37	Dark Câ€“V and Iâ€“V characteristics of silicon multi-junctions prepared by liquid-phase epitaxy. Vacuum, 1999, 55, 201-206.	1.6	6
38	TRANSPORT PROPERTIES OF n-POLYANILINE/p-POROUS SILICON HETEROJUNCTIONS. International Journal of Modern Physics B, 2007, 21, 5099-5111.	1.0	6
39	Structural and frequency dependencies of a.c. and dielectric characterizations of epitaxial InSb-based heterojunctions. Bulletin of Materials Science, 2016, 39, 1057-1063.	0.8	6
40	Stimulating photodiode characteristics of hybrid ZnPc-MWCNTs. Journal of Alloys and Compounds, 2022, 891, 161783.	2.8	6
41	Currentâ€“voltage characteristics and inhomogeneous barrier height analysis of Au/poly(o-toluidine)/p-Si/Al heterojunction diode. Journal of Materials Science: Materials in Electronics, 2014, 25, 3939-3946.	1.1	5
42	Morphological and crystalline structural characteristics of PEDOTâ„¢/TiO2 nanocomposites for applications towards technologyÂinÂelectronic devices. Journal of Alloys and Compounds, 2016, 671, 291-298.	2.8	4
43	Optical and electrical performance of ploypyrrol thin films and its hybrid junction applications. Optik, 2018, 172, 302-310.	1.4	4
44	Synthesis, characterization, and electrical properties of CuInGaSe2/SiO2/n-Si structure. Optical and Quantum Electronics, 2021, 53, 1.	1.5	4
45	Electrical and magnetic properties of Niâ€“Cuâ€“Si heterojunction prepared by the liquid phase epitaxy technique. Journal of Physics and Chemistry of Solids, 2010, 71, 1521-1526.	1.9	3
46	Fabrication, structural and electrical characterization of AlNi2Si based heterojunction grown by LPE. Materials Science in Semiconductor Processing, 2015, 35, 66-74.	1.9	3
47	Tuned high dielectric constant, low dielectric loss tangent with positive and negative values for PPy/MWCNTs/TiO₂/Al₂O₃/n-Si. Journal of Experimental Nanoscience, 2021, 16, 309-343.	1.3	3
48	Negative series resistance and photo-response properties of Au/PPY-MWCNTs composite/TiO₂/Al₂O₃/n-Si/Al photodiode. Materials Research Express, 2022, 9, 016301.	0.8	3
49	Synthesis and Characterization of Some Conducting Polymers and Their Complexed Compounds. Periodica Polytechnica: Chemical Engineering, 2014, 58, 35-41.	0.5	2
50	Carbon Nanotubes/N-Si Heterojunction with High Dielectric Constant and Rectification Ratio, Low Dielectric Loss Tangent. ECS Journal of Solid State Science and Technology, 0, , .	0.9	2
51	Preparation and Properties of Polyhydroxamic Acid and Poly(Vinyl Acetonyl Ketone) and Their Chelated Compounds. Energy Sources, Part A: Recovery, Utilization and Environmental Effects, 2013, 35, 1427-1440.	1.2	1
52	Structural and electrical performance of epitaxial InP based heterojunctions prepared by liquid phase epitaxy. Chinese Journal of Physics, 2019, 59, 83-91.	2.0	1
53	Photoresponsivity, Electrical and Dielectric Properties of GaAs/P-Si Heterojunction-Based Photodiode. Silicon, 0, , 1.	1.8	1
54	Novel Negative Capacitance and Conductance in All Temperatures and Voltages of Au/CNTs/n-Si/Al at Low and High Frequencies. ECS Journal of Solid State Science and Technology, 2021, 10, 111007.	0.9	1

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55	Novel Negative Capacitance Appeared in all Frequencies in Au/AlCu/SiO2/p-Si/Al Structure. Silicon, 2022, 14, 11061-11078.	1.8	1
56	The novel behavior of real and imaginary part of impedance, modulus, and AC conductivity of Au/PPyâ€“MWCNTs/TiO2/Al2O3/n-Si/Al. Journal of Materials Science: Materials in Electronics, 2022, 33, 11194.	1.1	1
57	Reviewâ€”The Negative Capacitance of a Novel Structure Au/PPy-MWCNTs/TiO₂/Al₂O₃/p-Si/Al. ECS Journal of Solid State Science and Technology, 2022, 11, 073008.	0.9	1
58	Characterization of epitaxial n-GaP/p-PSi heterojunctions. Journal of Surface Investigation, 2010, 4, 152-156.	0.1	0
59	Electronic properties and lateral inhomogeneous barrier heights of n-InP rods/p-Si heterojunction prepared by liquid phase epitaxy. Journal of Materials Science: Materials in Electronics, 2017, 28, 10488-10494.	1.1	0
60	Negative Series Resistance (Rs) and Real Part of Impedance (Z'), and Positive and Negative Imaginary Part of Impedance (Z'') at a High Frequency of Au/CNTS/n-Si/Al Structure. ECS Journal of Solid State Science and Technology, 0, , .	0.9	0